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DOCKET NO. SC12885TP

UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT

Marius Orlowski et al.

GROUP ART UNIT: 2823

APPLN. NO.:

10/631,093

EXAMINER:

Belur V. Keshavan

FILED:

July 31, 2003

CONFIRMATION No.: 1735

TITLE:

METHOD OF FORMING A TRANSISTOR HAVING

MULTIPLE CHANNELS AND STRUCTURE THEREOF

Certificate of Transmission under 37 C.F.R 1.8

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Signature

Printed Name of Person Signing Certificate

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

This paper is filed contemporaneous with the filing of the issue fee for this application. Entrance of the comments provided below regarding the statement of reasons for allowance provided by the Examiner is respectfully requested.

FEES

Applicants authorize the charging of Deposit Account No. 503079 (Freescale Semiconductor, Inc.) for any fees owed in connection with this application, or credit Deposit Account No. 503079 (Freescale Semiconductor, Inc.) for any refunds.

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REMARKS

In a communication mailed March 10, 2005, claims 13-25 were allowed. The Examiner provided a statement of reasons for allowance. To avoid the reasons from being construed out of context by implying that the points of novelty were completely contained in the sentences provided by the Examiner, Applicants are filing these remarks. Applicants submit that this application is distinguishable over the prior art due to the collective recitations in allowed independent claim 13. It is also Applicants' position that the claim recitals in the allowed dependent claims are also distinguishable over the prior art.

SEND CORRESPONDENCE TO:

Freescale Semiconductor, Inc.

Law Department

Customer Number: 23125

Respectfully submitted,

Robert L. King

Reg. No.: 30,185

Phone No.: 512-996-6839 Fax No.: 512-996-6853